



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Application of: WATANABE, Kenichi

Serial No.: 10/050,171

Filed: January 18, 2002

#8/Anita A
F. Tapp
2/12/03
Group Art Unit: 2815

Examiner: WARREN, Matthew E.

P.T.O. Confirmation No.: 7623

For: SEMICONDUCTOR DEVICE CAPABLE OF SUPPRESSING CURRENT CONCENTRATION IN PAD AND ITS MANUFACTURE METHOD

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

February 4, 2003

Sir:

In response to the Office Action dated November 6, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 7 and 9-13 as indicated below:

7. (Amended) A semiconductor device comprising:

a semiconductor substrate;

a first interlayer insulating film made of insulating material and formed on the semiconductor substrate;

a first intra-layer insulating film made of insulating material and formed on the first interlayer

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